

# NHUMB11/1/2 series

80 V, 100 mA PNP/PNP resistor-equipped double transistors
Rev. 1 — 23 July 2020 Product data sheet

## 1. General description

PNP/PNP Resistor-Equipped double Transistor (RET) family in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package.

**Table 1. Product overview** 

Type number	R1	R2 Pack		Package	NPN/NPN	NPN/PNP
	kΩ	kΩ	Nexperia	JEITA	complement:	complement:
NHUMB11	10	10	SOT363	SC-88	NHUMH11	NHUMD3
NHUMB1	22	22			NHUMH1	NHUMD2
NHUMB2	47	47			NHUMH2	NHUMD12

## 2. Features and benefits

- · 100 mA output current capability
- High breakdown voltage
- · Built-in resistors
- · Simplifies circuit design
- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

## 3. Applications

- · Digital applications
- Cost saving alternative for BC856 series in digital applications
- Controlling IC inputs
- Switching loads

## 4. Quick reference data

#### Table 2. Quick reference data

 $T_{amb}$  = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
Per transistor							
$V_{CEO}$	collector-emitter voltage	open base	-	-	-80	V	
Io	output current		-	-	-100	mA	



## 5. Pinning information

#### **Table 3. Pinning**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	GND1	GND (emitter) TR1	□6 □5 □4	O1 I2 GND2
2	I1	input (base) TR1		
3	O2	output (collector) TR2		R1 R2
4	GND2	GND (emitter) TR2		TR2
5	12	input (base) TR2		TR1 R2 R1
6	01	output (collector) TR1		
				GND1 I1 O2 aaa-019790

## 6. Ordering information

**Table 4. Ordering information** 

Type number	Package					
	Name	Description	Version			
NHUMB11	SC-88	plastic surface-mounted package; 6 leads	SOT363			
NHUMB1						
NHUMB2						

## 7. Marking

#### Table 5. Marking

3					
Type number	Marking code [1]				
NHUMB11	2B%				
NHUMB1	6C%				
NHUMB2	6E%				

[1] % = placeholder for manufacturing site code

## 8. Limiting values

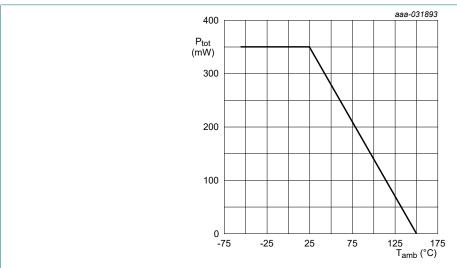
#### **Table 6. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

 $T_{amb}$  = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Max	Unit
Per transis	tor					
V <sub>CBO</sub>	collector-base voltage	open emitter		-	-80	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-80	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-10	V
V <sub>I</sub>	input voltage					
	NHUMB11			-40	+10	V
	NHUMB1			-60	+10	V
	NHUMB2			-80	+10	V
Io	output current			-	-100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	235	mW
Per device		<u> </u>		'		
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	350	mW
T <sub>j</sub>	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit-Board (PCB); single-sided copper; tin-plated and standard footprint.



FR4 PCB, single-sided copper, standard footprint

Fig. 1. Per device: Power derating curve SOT363 (SC-88)

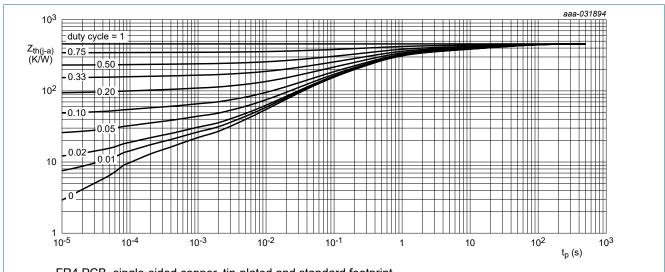
## 9. Thermal characteristics

#### **Table 7. Thermal characteristics**

 $T_{amb}$  = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Per transistor								
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1]	-	-	532	K/W	
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	150	K/W	
Per device								
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1]	-	-	358	K/W	

[1] Device mounted on an FR4 Printed-Circuit-Board (PCB); single-sided copper; tin-plated and standard footprint.



FR4 PCB, single-sided copper, tin-plated and standard footprint

Fig. 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

## 10. Characteristics

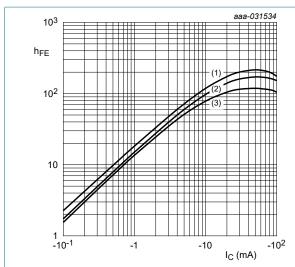
#### **Table 8. Characteristics**

 $T_{amb}$  = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit			
Per transis	tor									
V <sub>(BR)CBO</sub>	collector-base breakdown voltage	I <sub>C</sub> = -100 μA; I <sub>E</sub> = 0 A		-80	-	-	V			
V <sub>(BR)CEO</sub>	collector-emitter breakdown voltage	$I_C = -2 \text{ mA}; I_B = 0 \text{ A}$		-80	-	-	V			
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = -80 \text{ V}; I_E = 0 \text{ A}$	$V_{CB} = -80 \text{ V}; I_E = 0 \text{ A}$		-	-100	nA			
I <sub>CEO</sub>	collector-emitter cut-off	V <sub>CE</sub> = -60 V; I <sub>B</sub> = 0 A		-	-	-100	nA			
	current	V <sub>CE</sub> = -60 V; I <sub>B</sub> = 0 A; T <sub>j</sub> = 150 °C		-	-	-5	μΑ			
I <sub>EBO</sub>	emitter-base cut-off curr	emitter-base cut-off current								
	NHUMB11	V <sub>EB</sub> = -7 V; I <sub>C</sub> = 0 A		-	-	-600	μA			
	NHUMB1				-	-270	μΑ			
	NHUMB2					-130	μA			
h <sub>FE</sub>	DC current gain									
	NHUMB11	V <sub>CE</sub> = -5 V; I <sub>C</sub> = -10 mA		50	-	-				
	NHUMB1			70	-	-				
	NHUMB2			100	-	-				
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = -10 mA; I <sub>B</sub> = -0.5 mA		-	-	-100	mV			
V <sub>I(off)</sub>	off-state input voltage	V <sub>CE</sub> = -5 V ; I <sub>C</sub> = -100 μA		-	-1.15	-0.8	V			
V <sub>I(on)</sub>	on-state input voltage									
	NHUMB11	V <sub>CE</sub> = -0.3 V ; I <sub>C</sub> = -10 mA		-2.5	-1.8	-	V			
	NHUMB1				-2.3	-	V			
	NHUMB2			-5	-3.3	-	V			
R1	bias resistor 1 (input)	bias resistor 1 (input) [1]								
	NHUMB11			7	10	13	kΩ			
	NHUMB1			15.4	22	28.6	kΩ			
	NHUMB2			33	47	61	kΩ			
R2/R1	bias resistor ratio		[1]	8.0	1	1.2				
f <sub>T</sub>	transition frequency	V <sub>CE</sub> = -5 V; I <sub>C</sub> = -10 mA; f = 100 MHz	[2]	-	150	-	MHz			
C <sub>c</sub>	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = I_e = 0 \text{ A}; f = 1 \text{ MHz}$		-	-	3	рF			

<sup>[1]</sup> See section "Test information" for resistor calculation and test conditions

<sup>[2]</sup> Characteristics of built-in transistor



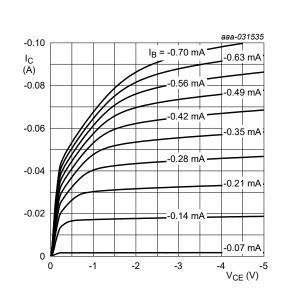
$$V_{CE} = -5 V$$

(1) 
$$T_{amb}$$
 = 100 °C

(2) 
$$T_{amb}$$
 = 25 °C

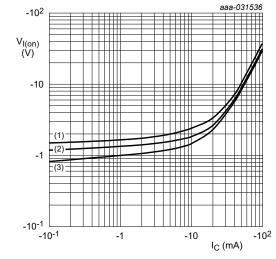
(3) 
$$T_{amb} = -40 \, ^{\circ}C$$

Fig. 3. NHUMB11: DC current gain as a function of collector current; typical values



 $T_{amb}$  = 25 °C

Fig. 4. NHUMB11: Collector current as a function of collector-emitter voltage; typical values

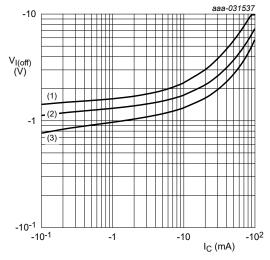


$$V_{CE}$$
 = -0.3  $V$ 

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

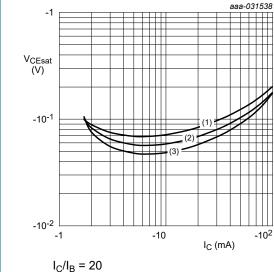
Fig. 5. NHUMB11: On-state input voltage as a function of collector current; typical values



$$V_{CE} = -5 V$$

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

Fig. 6. NHUMB11: Off-state input voltage as a function of collector current; typical values

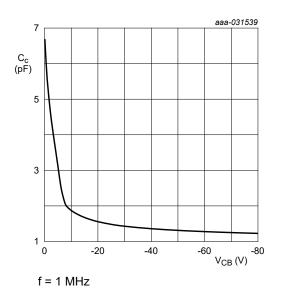


(1)  $T_{amb}$  = 100 °C

(2)  $T_{amb}$  = 25 °C

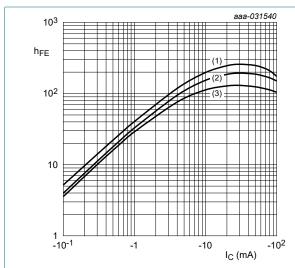
(3)  $T_{amb} = -40 \, ^{\circ}C$ 

**NHUMB11:** Collector-emitter saturation voltage Fig. 7. as a function of collector current; typical values



 $T_{amb}$  = 25 °C

Fig. 8. NHUMB11: Collector capacitance as a function of collector-base voltage; typical values



 $V_{CF} = -5 V$ 

(1)  $T_{amb} = 100 \, ^{\circ}C$ 

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = -40 \, ^{\circ}C$ 

NHUMB1: DC current gain as a function of Fig. 9. collector current; typical values

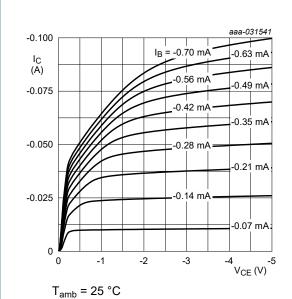
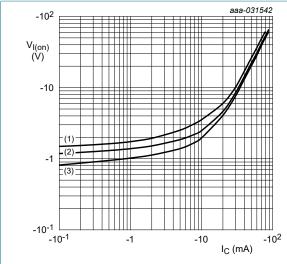


Fig. 10. NHUMB1: Collector current as a function of collector-emitter voltage; typical values



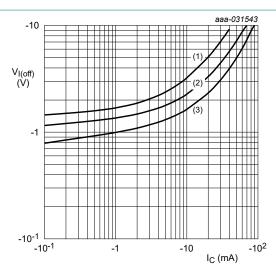
$$V_{CE}$$
 = -0.3  $V$ 

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 11. NHUMB1: On-state input voltage as a function of collector current; typical values



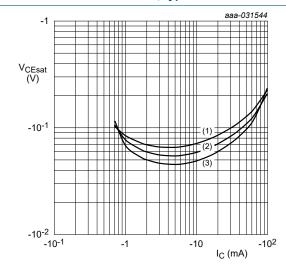
$$V_{CE} = -5 V$$

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 12. NHUMB1: Off-state input voltage as a function of collector current; typical values



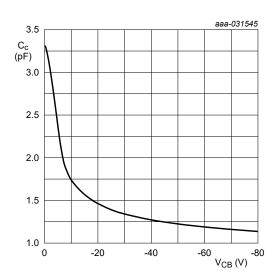
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

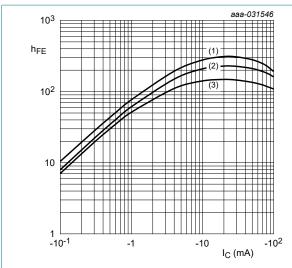
(3) 
$$T_{amb} = -40 \, ^{\circ}C$$

Fig. 13. NHUMB1: Collector-emitter saturation voltage as a function of collector current; typical values



f = 1 MHz

Fig. 14. NHUMB1: Collector capacitance as a function of collector-base voltage; typical values

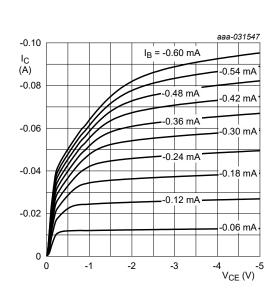


$$V_{CE} = -5 V$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

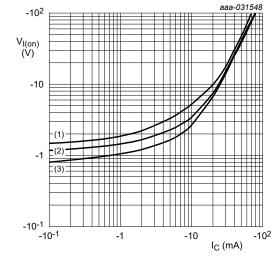
(3) 
$$T_{amb} = -40 \, ^{\circ}C$$

Fig. 15. NHUMB2: DC current gain as a function of collector current; typical values



 $T_{amb}$  = 25 °C

Fig. 16. NHUMB2: Collector current as a function of collector-emitter voltage; typical values

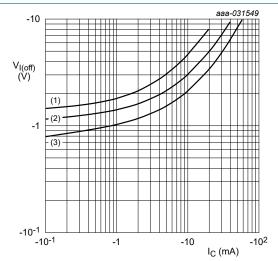


 $V_{CE}$  = -0.3 V

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

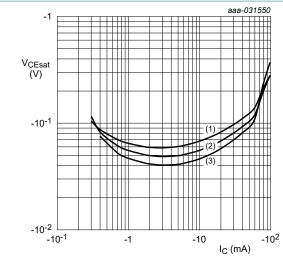
Fig. 17. NHUMB2: On-state input voltage as a function of collector current; typical values



$$V_{CE} = -5 V$$

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

Fig. 18. NHUMB2: Off-state input voltage as a function of collector current; typical values

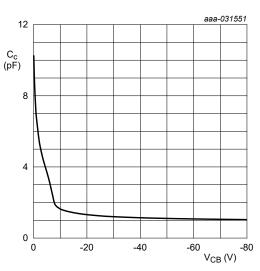


 $I_{\rm C}/I_{\rm B} = 20$ 

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(3) 
$$T_{amb} = -40 \, ^{\circ}C$$

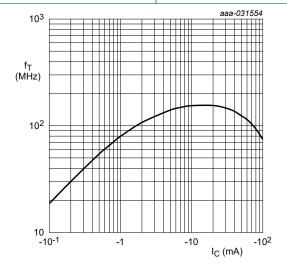
Fig. 19. NHUMB2: Collector-emitter saturation voltage as a function of collector current; typical values



f = 1 MHz

 $T_{amb}$  = 25 °C

Fig. 20. NHUMB2: Collector capacitance as a function of collector-base voltage; typical values of built-in transistor



f = 100 MHz

 $V_{CE} = -5 V$ 

T<sub>amb</sub> = 25 °C

Fig. 21. Transition frequency as a function of collector current; typical values of built-in transistor

## 11. Test information

#### **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

#### **Resistor calculation**

Calculation of bias resistor 1 (R1)

$$R_I = \frac{V(I_{I2}) - V(I_{II})}{I_{I2} - I_{II}}$$

Calculation of bias resistor ratio (R2/R1)

$$\frac{R2}{R1} = \frac{V(I14) - V(I13)}{R1 \cdot (I14 - I13)} - 1$$

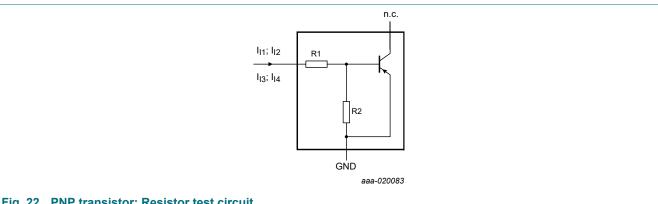


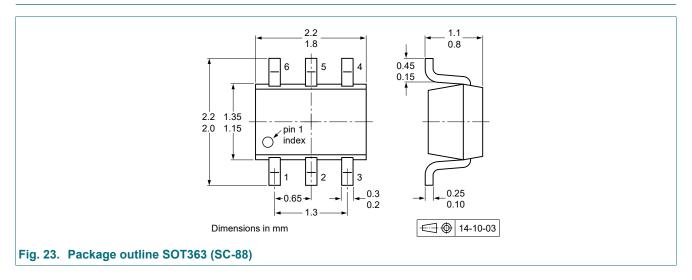
Fig. 22. PNP transistor: Resistor test circuit

#### **Resistor test conditions**

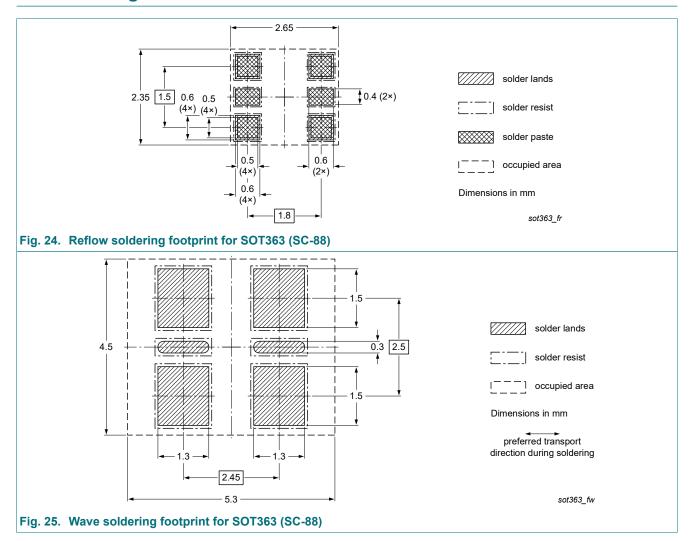
Table 9. Resistor test conditions

Type number	R1 (kΩ)	R2 (kΩ)	Test conditi	Test conditions				
			I <sub>I1</sub>	I <sub>I2</sub>	I <sub>I3</sub>	I <sub>14</sub>		
Per transistor								
NHUMB11	10	10	-800 µA	-1.1 mA	350 μΑ	450 μΑ		
NHUMB1	22	22	-550 μA	-750 μA	150 µA	230 μΑ		
NHUMB2	47	47	-250 μA	-350 µA	55 μΑ	105 µA		

## 12. Package outline



## 13. Soldering



## 14. Revision history

#### Table 10. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
NHUMB11_1_2_SER v.1	20200723	Product data sheet	-	-

## 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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